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April 1st, 2010 Renesas Electronics Corporation

Issued by: Renesas Electronics Corporation (http://www.renesas.com)

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RJK0365DPA

Silicon N Channel Power MOS FET Power Switching

REJ03G1655-0300 Rev.3.00 Aug 05, 2008

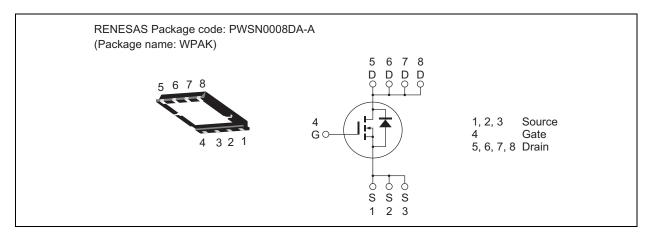
Features

- High speed switching
- Capable of 4.5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)}\!=7.0~\text{m}\Omega$ typ. (at $V_{GS}\!=10~\text{V})$

• Pb-free

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | Unit |
|--|-----------------------------|-------------|------|
| Drain to source voltage | V _{DSS} | 30 | V |
| Gate to source voltage | V _{GSS} | ±20 | V |
| Drain current | I _D | 30 | A |
| Drain peak current | I _{D(pulse)} Note1 | 120 | A |
| Body-drain diode reverse drain current | I _{DR} | 30 | A |
| Avalanche current | I _{AP} Note 2 | 12 | A |
| Avalanche energy | E _{AR} Note 2 | 14.4 | mJ |
| Channel dissipation | Pch Note3 | 30 | W |
| Channel to case thermal resistance | θch-c Note3 | 4.17 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

2. Value at Tch = 25°C, Rg \geq 50 Ω

3. $Tc = 25^{\circ}C$

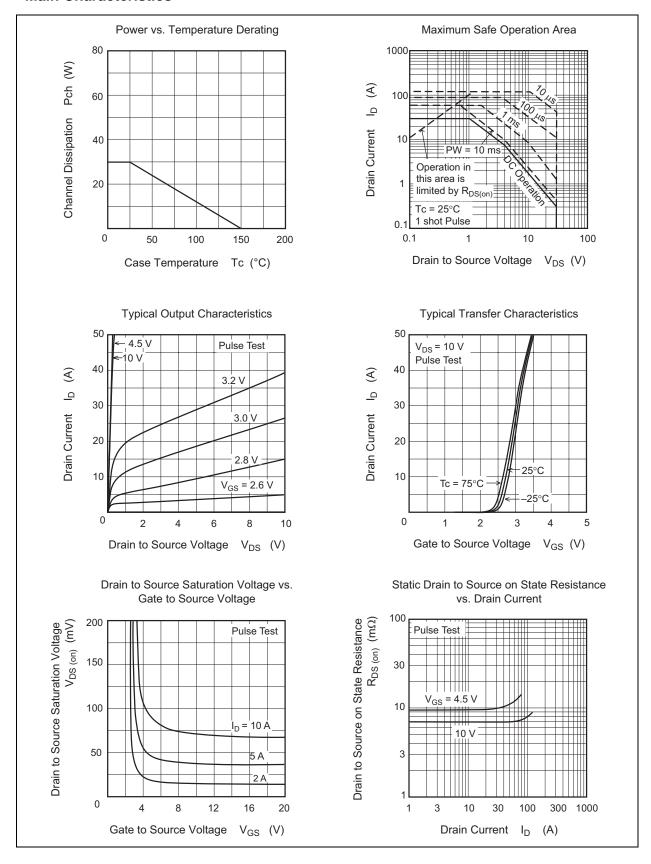
Electrical Characteristics

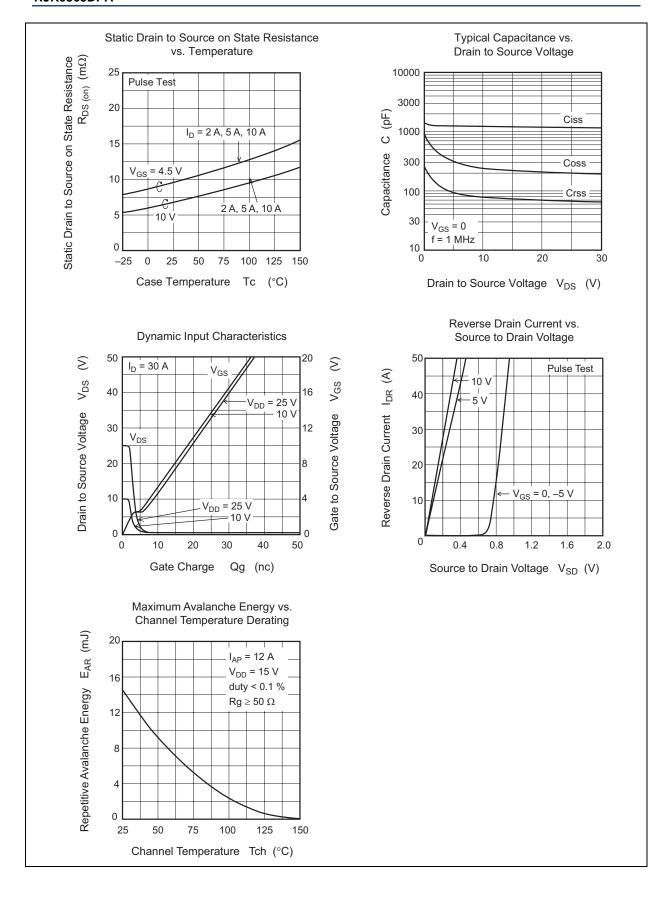
 $(Ta = 25^{\circ}C)$

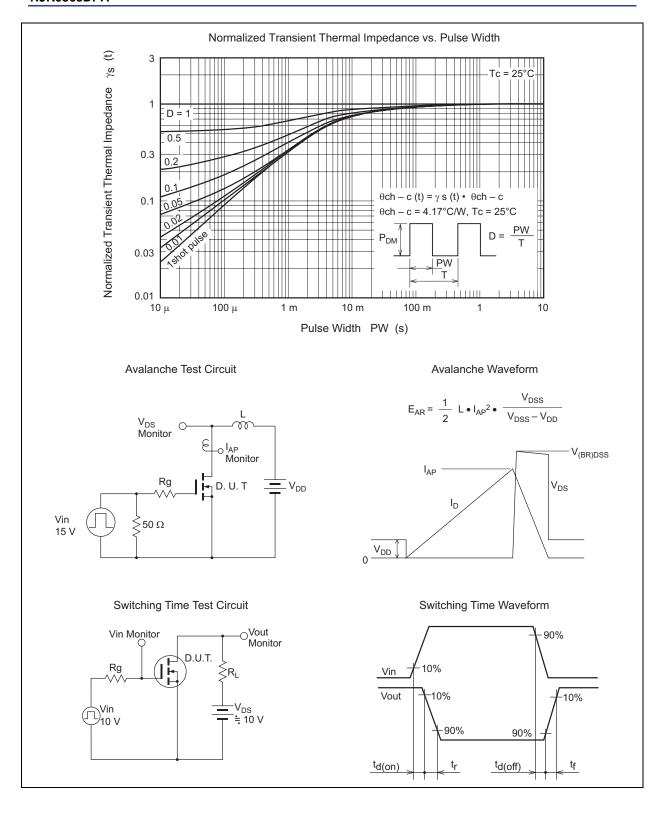
| Item | Symbol | Min | Тур | Max | Unit | Test Conditions | |
|-----------------------------------|---------------------|-----|------|-------|------|---|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 30 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ | |
| Gate to source leak current | I _{GSS} | _ | _ | ± 0.1 | μΑ | $V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$ | |
| Zero gate voltage drain current | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 30 \text{ V}, V_{GS} = 0$ | |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 1.2 | _ | 2.5 | V | $V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA}$ | |
| Static drain to source on state | R _{DS(on)} | _ | 7.0 | 9.1 | mΩ | I _D = 15 A, V _{GS} = 10 V Note4 | |
| resistance | R _{DS(on)} | _ | 9.6 | 13.4 | mΩ | $I_D = 15 \text{ A}, V_{GS} = 4.5 \text{ V}^{\text{Note4}}$ | |
| Forward transfer admittance | y _{fs} | _ | 60 | _ | S | $I_D = 15 \text{ A}, V_{DS} = 10 \text{ V}^{\text{Note4}}$ | |
| Input capacitance | Ciss | _ | 1180 | _ | pF | V _{DS} = 10 V | |
| Output capacitance | Coss | _ | 230 | _ | pF | $V_{GS} = 0$ | |
| Reverse transfer capacitance | Crss | _ | 80 | _ | pF | f = 1 MHz | |
| Gate Resistance | Rg | _ | 0.8 | _ | Ω | | |
| Total gate charge | Qg | _ | 7.6 | _ | nC | V _{DD} = 10 V | |
| Gate to source charge | Qgs | _ | 3.0 | _ | nC | V _{GS} = 4.5 V | |
| Gate to drain charge | Qgd | _ | 1.7 | _ | nC | $I_D = 30 \text{ A}$ | |
| Turn-on delay time | t _{d(on)} | _ | 5.4 | _ | ns | V _{GS} = 10 V, I _D = 15 A | |
| Rise time | t _r | _ | 4.0 | _ | ns | $V_{DD} \cong 10 \text{ V}$ | |
| Turn-off delay time | t _{d(off)} | _ | 34 | _ | ns | $R_L = 0.66 \Omega$ | |
| Fall time | t _f | _ | 4.3 | _ | ns | $Rg = 4.7 \Omega$ | |
| Body-drain diode forward voltage | V_{DF} | _ | 0.87 | 1.13 | V | $I_F = 30 \text{ A}, V_{GS} = 0^{\text{Note4}}$ | |
| Body-drain diode reverse recovery | t _{rr} | _ | 20 | _ | ns | $I_F = 30 \text{ A}, V_{GS} = 0$ | |
| time | | | | | | $di_F/dt = 100 A/ \mu s$ | |

Notes: 4. Pulse test

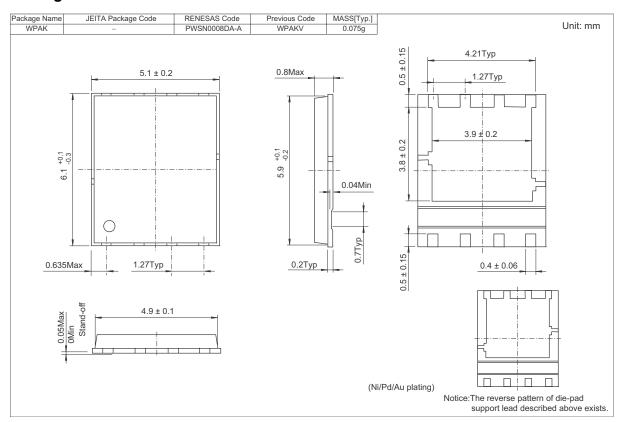
Main Characteristics







Package Dimensions



Ordering Information

| Part No. | Quantity | Shipping Container | | |
|------------------|----------|--------------------|--|--|
| RJK0365DPA-00-J0 | 2500 pcs | Taping | | |

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